

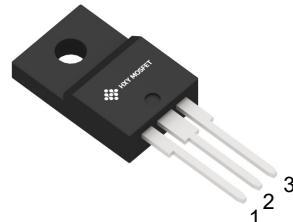


Features

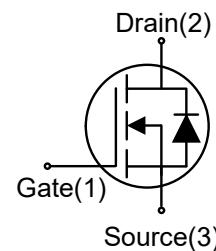
- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low On-Resistance
- Avalanche Ruggedness

Applications

- Solar Inverters
- Switch Mode Power Supplies
- Battery Chargers
- High Voltage DC/DC Converters



TO-220F



Package Marking and Ordering Information

Ordering Part Number	Package	Brand
R6530ENXC7G	TO-220F	HXY MOSFET

Maximum Ratings (T_C = 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
V _{DSmax}	Drain - Source Voltage	650	V	
V _{GSmax}	Gate - Source Voltage (dynamic)	-8/+22	V	
V _{GS}	Gate - Source Voltage	-4/+18	V	
I _D	Continuous Drain Current	24	A	T _C = 25°C
		13		T _C = 125°C
I _{D(pulse)}	Pulsed Drain Current	50	A	Pulse width t _P limited by T _{jmax}
P _D	Power Dissipation	95	W	T _C = 25°C
T _J , T _{stg}	Operating Junction and Storage Temperature	-55 to +175	°C	
I _S	Source current(Body Diode)	24	A	T _C = 25°C
		13		T _C = 125°C
E _{AS}	Avalanche energy, single pulse	265	mJ	L=10mH

• Example of acceptable V_{GS} waveform





Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristics						
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	650	-	-	V	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=100\mu\text{A}$
$V_{\text{GS}(\text{th})}$	Gate threshold voltage	2	3	4	V	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=2\text{mA}$
I_{DSS}	Zero gate voltage drain current	-	1	5	μA	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$ $T_c=25^\circ\text{C}$ $T_c=175^\circ\text{C}$
I_{GSS}	Gate-source leakage current	-		100	nA	$V_{\text{GS}}=18\text{V}, V_{\text{DS}}=0\text{V}$
$R_{\text{DS}(\text{on})}$	Drain-source on-state resistance	-	110	140	$\text{m}\Omega$	$V_{\text{GS}}=18\text{V}, I_{\text{D}}=7\text{A},$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$
$R_{\text{DS}(\text{on})}$	Drain-source on-state resistance	-	145	200	$\text{m}\Omega$	$V_{\text{GS}}=15\text{V}, I_{\text{D}}=7\text{A},$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$
Dynamic Characteristics						
C_{iss}	Input Capacitance	-	508.0	-	pF	$V_{\text{DS}} = 400\text{V}$ $V_{\text{GS}} = 0\text{V}$ $T_j = 25^\circ\text{C}$ $V_{\text{AC}}=25\text{mV}$ $f = 1\text{MHz}$
C_{oss}	Output Capacitance	-	33.0	-		
C_{rss}	Reverse Transfer Capacitance	-	3.2	-		
Q_{G}	Gate Total Charge		30.5	-	nC	$V_{\text{DS}} = 400\text{V}$ $V_{\text{GS}} = 0/+18\text{V}$ $I_{\text{D}} = 7\text{A}$ $I_{\text{G}}=10\text{mA}$
Q_{gs}	Gate-Source charge	-	2.55	-		
Q_{gd}	Gate-Drain charge	-	7.9	-		
E_{ON}	Turn-On Switching Energy	-	101	-	uJ	$V_{\text{DD}} = 400\text{V}$ $V_{\text{GS}} = -4/+18\text{V}$ $I_{\text{D}} = 7\text{A}$ $R_{\text{G}} = 5\Omega$ $L = 1\text{mH}$ $T_j = 25^\circ\text{C}$
E_{OFF}	Turn-Off Switching Energy	-	23	-		
$t_{\text{d}(\text{on})}$	Turn-on delay time	-	6.5	-		
t_r	Rise time	-	3.1	-	ns	
$t_{\text{d}(\text{off})}$	Turn-off delay time	-	29.5	-		
t_f	Fall time	-	18.5	-		
R_{G}	Gate resistance	-	3.0	-	Ω	$V_{\text{AC}} = 25\text{mV}, f=1\text{MHz}$



Body Diode Characteristics

V_{SD}	Body Diode Forward Voltage	-	4.2	-	V	$V_{GS}=-4V, I_{SD}=3.5A, T_J=25^{\circ}C$
		-	3.8	-		$V_{GS}=-4V, I_{SD}=3.5A, T_J=175^{\circ}C$
t_{rr}	Reverse Recovery Time	-	42.2	-	ns	$V_R = 600V$ $I_D = 7A$ $di/dt = 1000A/\mu s$ $V_{GS} = -4V$ $T_J = 25^{\circ}C$
Q_{rr}	Reverse Recovery Charge	-	66	-	nC	
E_{REC}	Reverse Recovery Energy	-	14.74	-	uJ	
I_{rrm}	Peak Reverse Recovery Current	-	4.67	-	A	
t_A	Charge Time	-	20.8	-	ns	
t_B	DisCharge Time	-	21.4	-	ns	

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions
R_{thJC}	Thermal Resistance from Junction to Case	1.55	°C/W	
R_{thJA}	Thermal Resistance From Junction to Ambient	40		



Typical Performance

Fig 1. Output Characteristics ($T_J = -55^\circ\text{C}$)

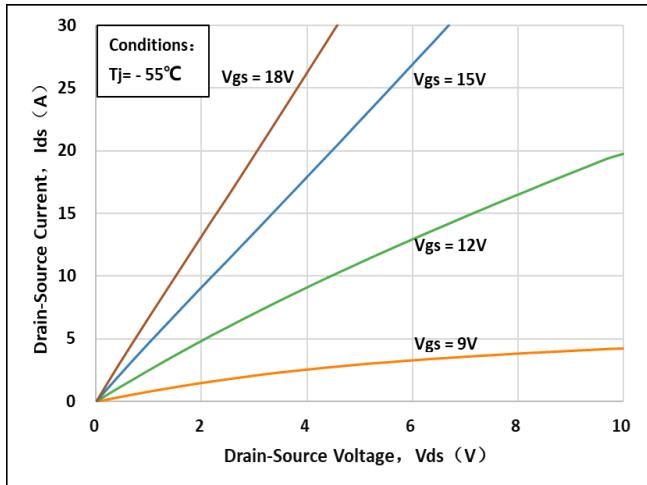


Fig 2. Output Characteristics ($T_J = 25^\circ\text{C}$)

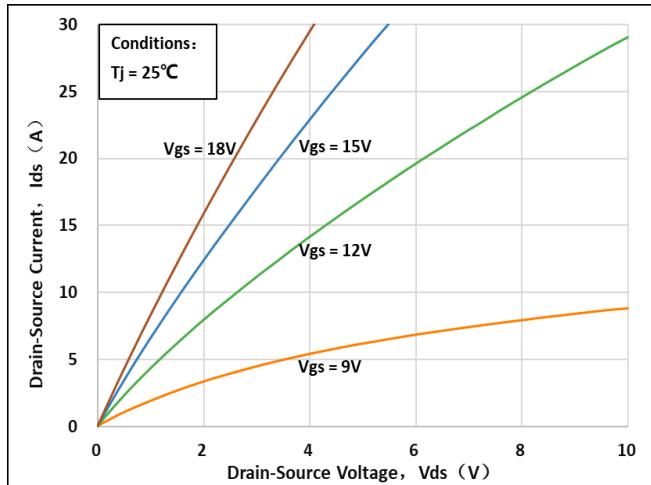


Fig 3. Output Characteristics ($T_J = 175^\circ\text{C}$)

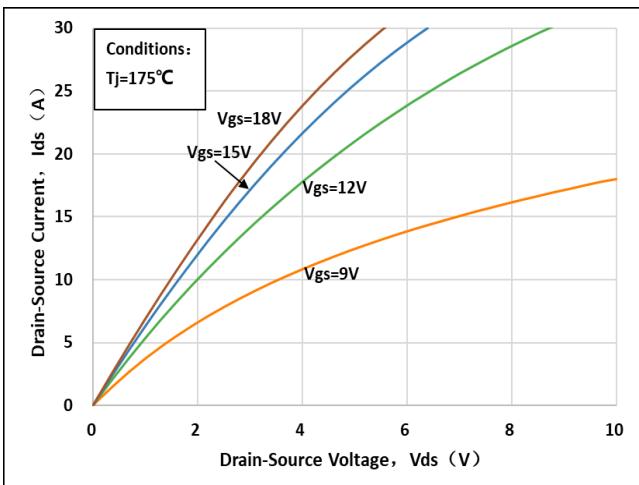


Fig 4: R_{dson} Vs Id_s Characteristics

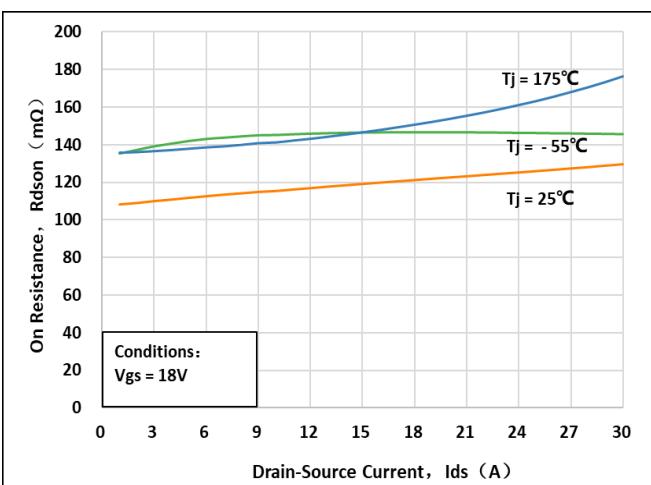


Fig 5: $R_{ds(on)}$ vs. Temperature

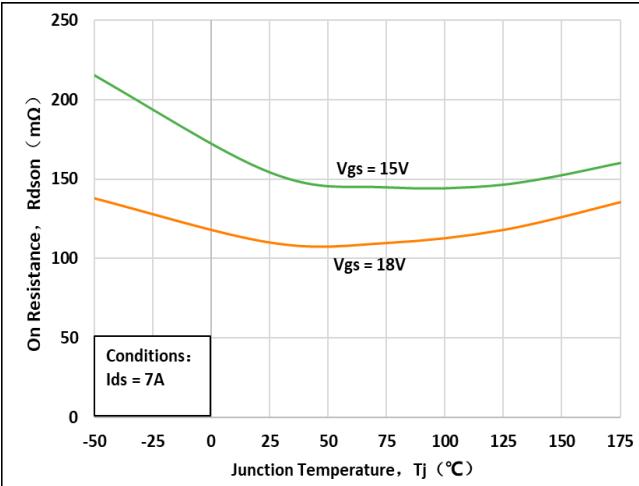


Fig 6: Transfer Characteristics

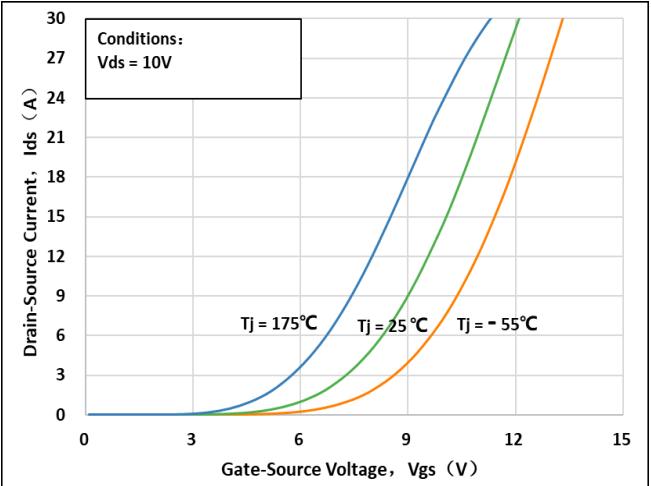




Fig 7: Body-diode Characteristics ($T_J = -55^\circ\text{C}$)

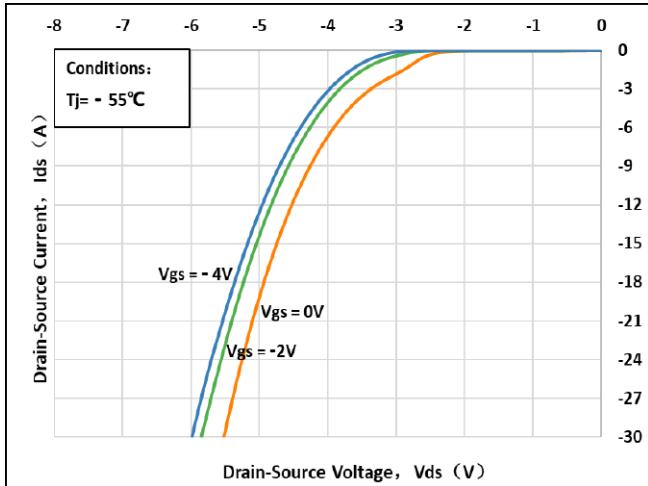


Fig 8: Body-diode Characteristics ($T_J = 25^\circ\text{C}$)

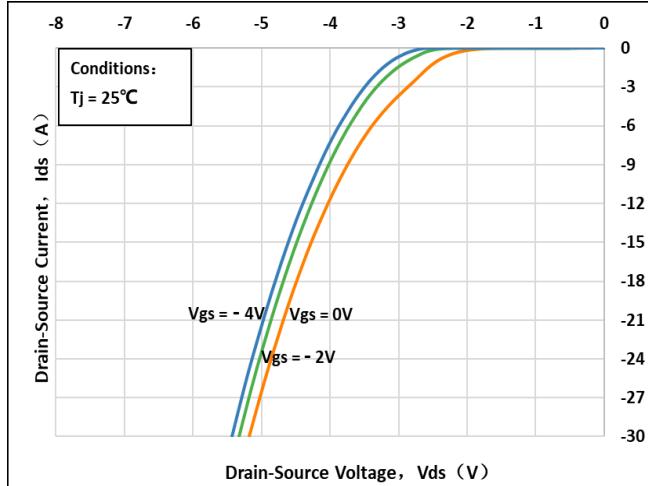


Fig 9: Body-diode Characteristics ($T_J = 175^\circ\text{C}$)

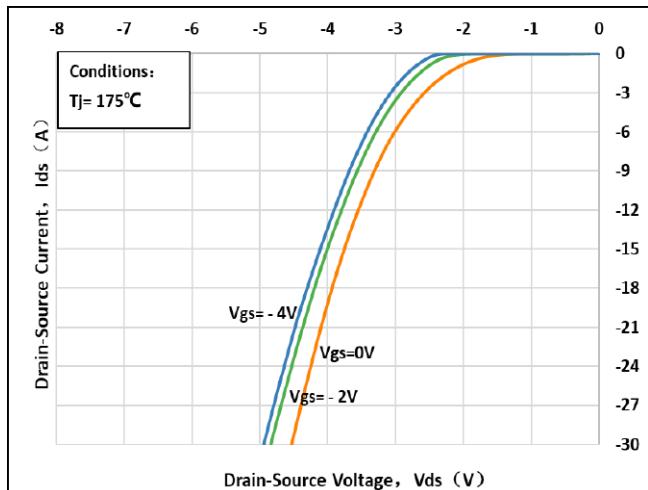


Fig 10: V_{th} Vs T_J Temperature Characteristics

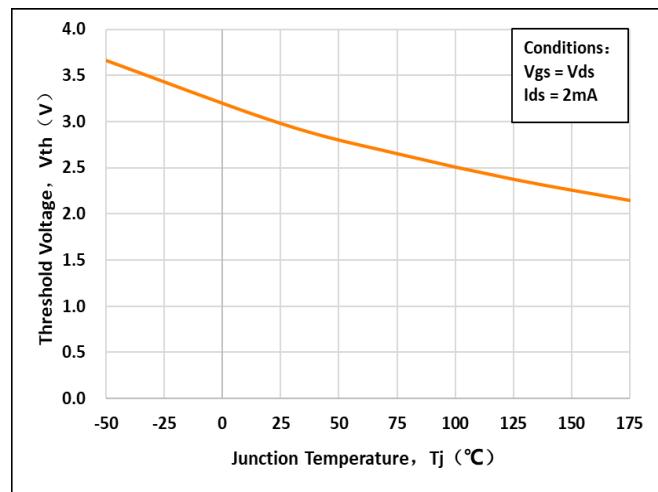


Fig 11: 3rd Quadrant Characteristics ($T_J = -55^\circ\text{C}$)

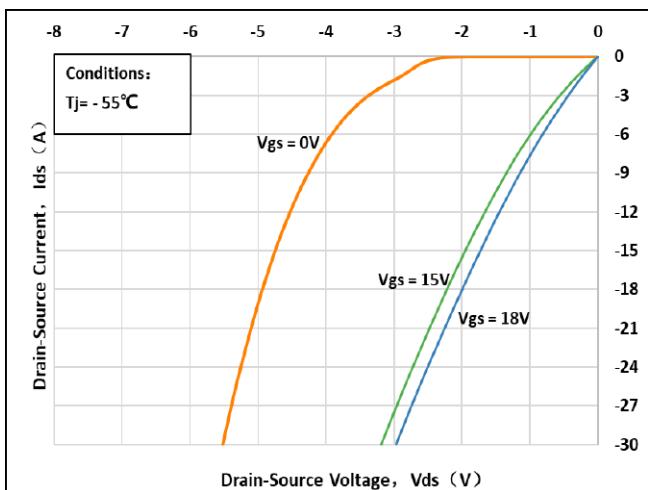


Fig 12: 3rd Quadrant Characteristics ($T_J = 25^\circ\text{C}$)

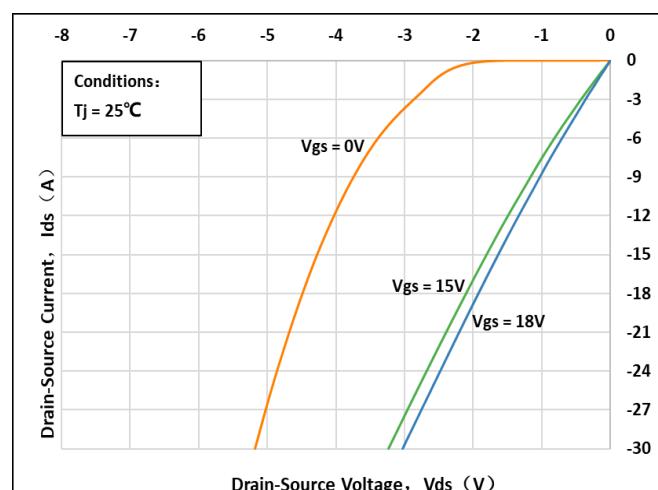




Fig 13: 3rd Quadrant Characteristics($T_j=175^\circ\text{C}$)

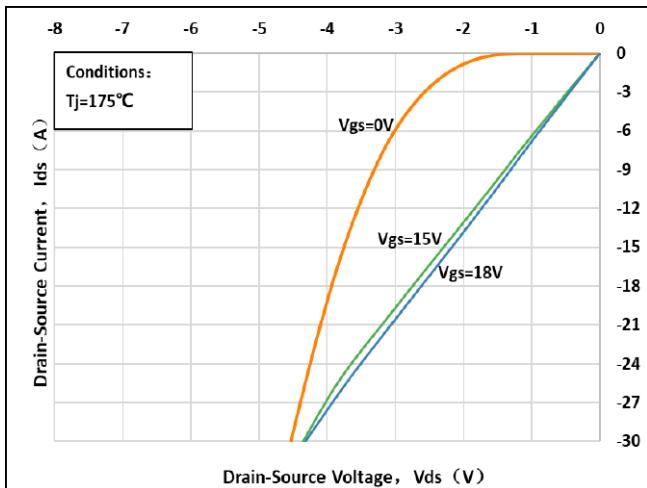


Fig 14: Gate Charge Characteristics

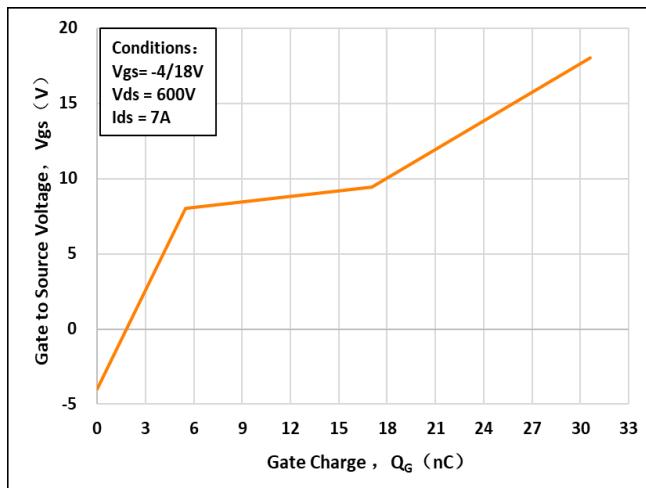


Fig 15: Drain Current vs.Case Temperature

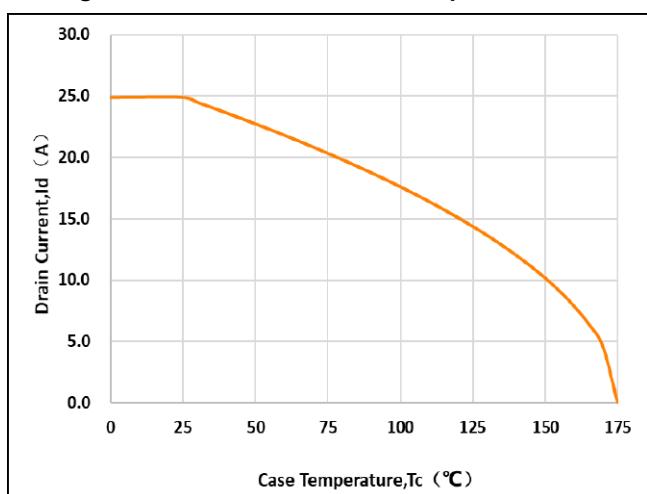


Fig 16: Safe Operating Area

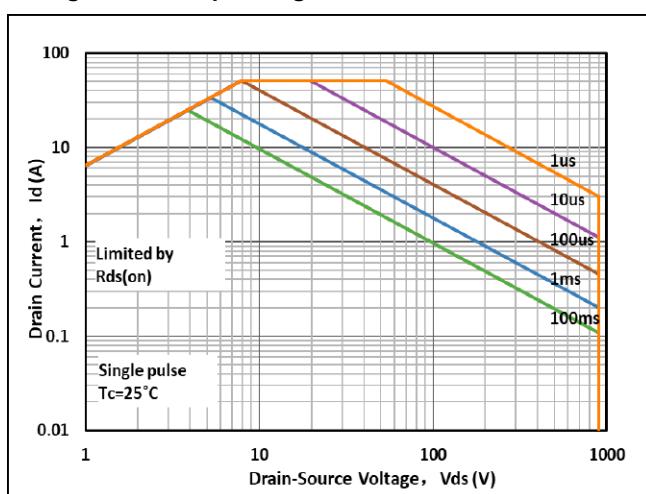


Fig 17: Capacitance Characteristics

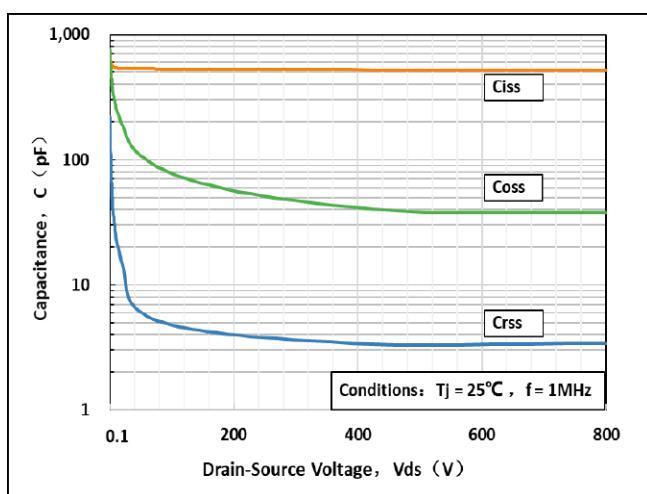
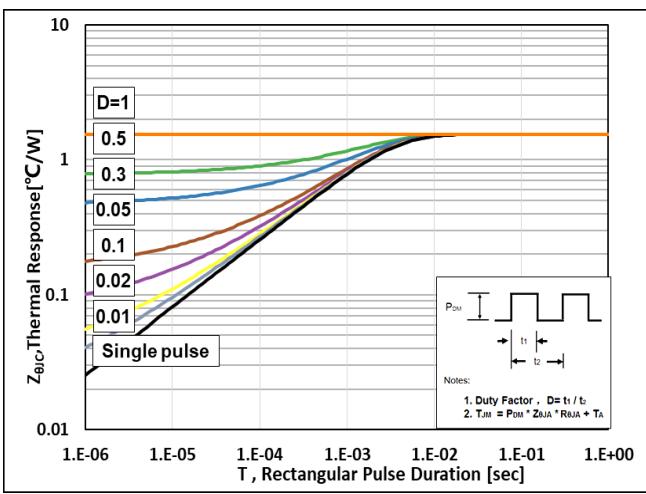


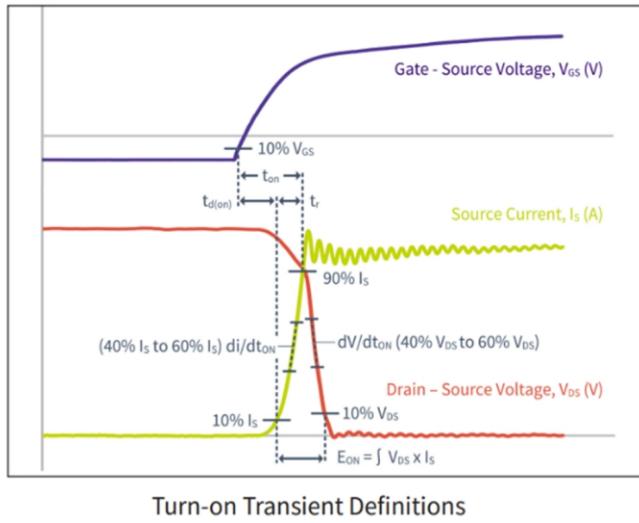
Fig 18: Transient Thermal Impedance



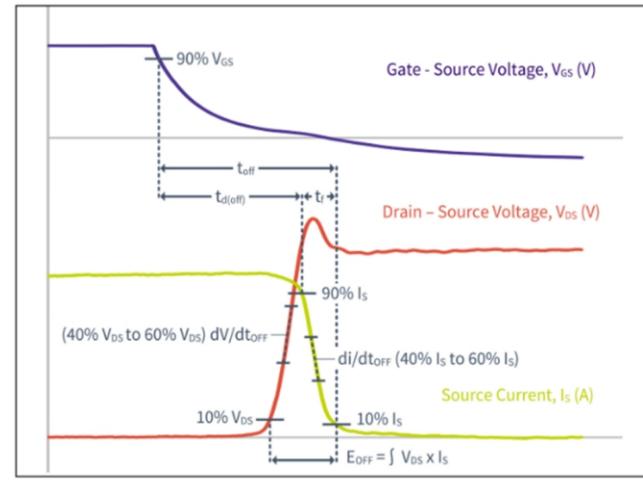


Test Circuit & Waveform

Figure A. Definition of switching times



Turn-on Transient Definitions



Turn-off Transient Definitions

Figure B. Dynamic test circuit

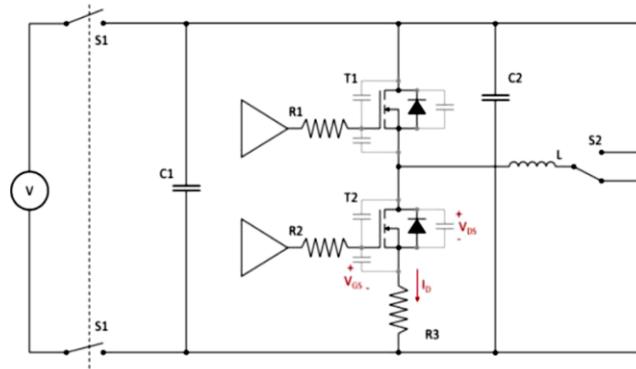
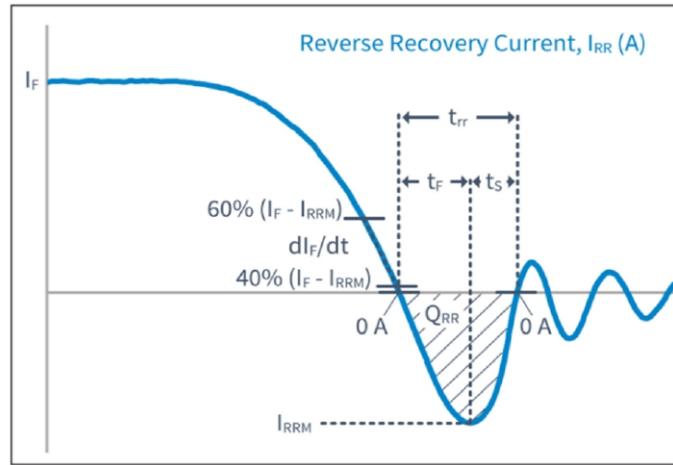


Figure C. Definition of body diodeswitching characteristics

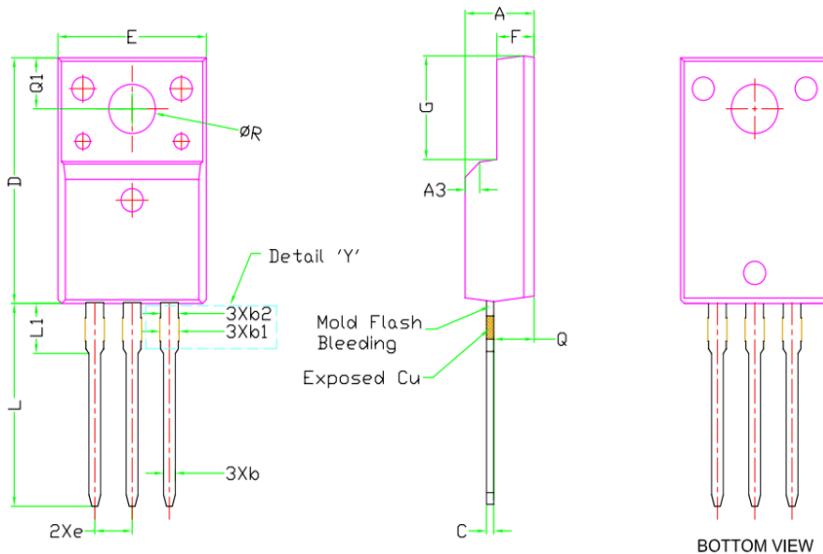


Reverse Recovery Definitions



Package Dimensions

Package TO-220F



BOTTOM VIEW

SYMBOL	DIMENSIONS		
	Min.	Nom.	Max.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e		2.54	
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
ΦR	3.08	3.18	3.28



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